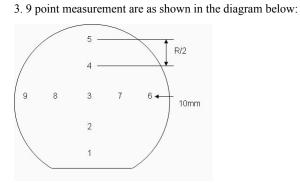
Icemos Technology Ltd Product Specification 1001.338002 Issue Date 09 January 2014 10:5

Part Number	Customer	

Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Edge Rounding	Semi M1	Wafer Vendor
	6.0	Overall Thickness	563.00 +/- 12.00 μm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<3.00μm	Guaranteed by Process
	9.0	Bow	<50.00μm	ADE to ASTM F534, 20%
	10.0	Warp	<50.00μm	ADE to ASTM F657, 20%
	11.0	Edge Chips	0	Bright Light, 100% (note 2)
	12.0	Edge Exclusion	5mm	
HandleSilicon	13.0	Handle Growth Method	CZ or FZ	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	15.0	Handle Doping Type	N or P	Wafer Vendor
	16.0	Handle Dopant	ANY	Wafer Vendor
	17.0	Handle Resistivity	1 - 1000 Ohmem	Wafer Vendor
	18.0	Handle Thickness	550.00 +/- 10.00 um	ADE, 100%inspection
	19.0	Backside Finish	ANY Sacraficial layer	Guaranteed by Process
BuriedOxide	20.0	Oxide formed on	Both handle and device	
	21.0	Oxide Thickness	10,000.00 +/- 1,000.00 A	
DeviceSilicon	31.0	Device Growth Method	CZ	Wafer Vendor
	32.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	33.0	Device Doping Type	N	Wafer Vendor
	34.0	Device Dopant	Phosphorous	Wafer Vendor
	35.0	Device Resistivity	1 - 3 Ohmem	Wafer Vendor
	36.0	Nominal Thickness	12.00 +/- 0.75 um	FTIR or Filmetrics 9 point measurement
	37.0	Distance to device silicon edge from wafer edge	<2mm	Guaranteed by process
	39.0	Voids	none inside 5mm edge exclusion	Bright Light inspection 100%
	40.0	Scratches	none	Bright Light inspection 100%
	41.0	Haze	none	Bright Light inspection

Page 1 of 2 13/01/2021 www.icemostech.com

Part Number		Customer	
Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspec	etion performed using microscope scan as below. 5x objective.	
		pections performed exclude all wafer area outside the edge exclusi on. High intensity bright lamp inspection as per ASTM F523.	on defined in Overall



Additional Information